

Description

- 1) A package of series of two chips.
- 2) With high thermal conductivity DBC as the insulation.
- 3) Welding by vacuum welding technology, which provide high reliability.



Typical Application

DC motor control, temperature control and light control system.

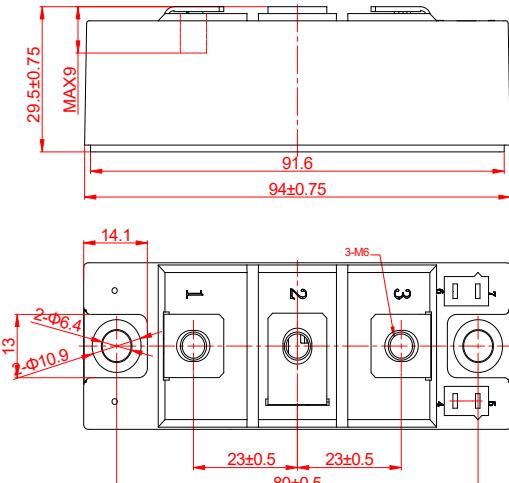
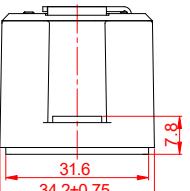
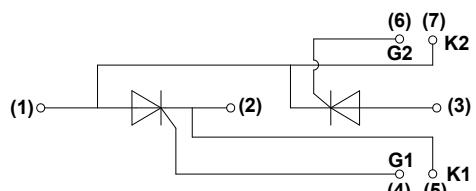
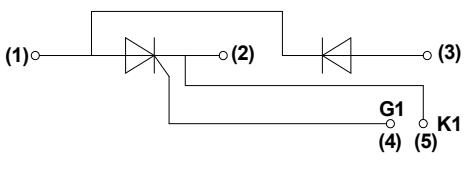
Absolute Maximum Ratings (Packaged into modules, unless otherwise specified, $T_{CASE}=25^{\circ}\text{C}$)

Parameter	Test Conditions	Symbol	Values			Unit
			12	16	18	
Operating junction temperature range		T_j	-40~125			°C
Storage temperature range		T_{stg}	-40~125			°C
Repetitive peak off-state voltage	$T_j=25^{\circ}\text{C}$	V_{DRM}	1200	1600	1800	V
Repetitive peak reverse voltage	$T_j=25^{\circ}\text{C}$	V_{RRM}	1200	1600	1800	V
Non-repetitive peak off-state voltage	$T_j=25^{\circ}\text{C}$	V_{DSM}	1300	1700	1900	V
Non-repetitive peak reverse voltage	$T_j=25^{\circ}\text{C}$	V_{RSM}	1300	1700	1900	V
Average on-state current	$T_c=85^{\circ}\text{C}$	$I_{T(AV)}/I_{F(AV)}$	160			A
Peak on-state surge current	$t_p=10\text{ms } V_R=0.6V_{RRM}$	I_{TSM}/I_{FSM}	3200			A
I^2t value for fusing	$t_p=10\text{ms } V_R=0.6V_{RRM}$	I^2t	51200			A^2s
Critical rate of rise of on-state current	$I_G=2 \times I_{GT}$	dI/dt	150			$\text{A}/\mu\text{s}$
Insulation voltage	A.C 50Hz(1s/1min)	V_{ISO}	3600/3000			V

Electrical Characteristics (Packaged into modules, unless otherwise specified, $T_{CASE}=25^{\circ}\text{C}$)

Parameter	Test Conditions	Symbol	Values	Unit
Peak on-state voltage	$I_T=480\text{A}$ $t_P=380\mu\text{s}$	V_{TM}	≤ 1.8	V
Threshold voltage	$T_j=125^{\circ}\text{C}$	V_{TO}	≤ 0.95	V
Dynamic resistance	$T_j=125^{\circ}\text{C}$	R_d	≤ 1.65	$\text{m}\Omega$
Repetitive peak off-state current	$V_D=V_{DRM}$ $T_c=25^{\circ}\text{C}$ $T_c=125^{\circ}\text{C}$	I_{DRM1} I_{DRM2}	≤ 100 ≤ 50	μA mA
Repetitive peak reverse current	$V_R=V_{RRM}$ $T_c=25^{\circ}\text{C}$ $T_c=125^{\circ}\text{C}$	I_{RRM1} I_{RRM2}	≤ 100 ≤ 50	μA mA
Triggering gate current	$V_D=12\text{V}$ $R_L=30\Omega$	I_{GT}	20-120	mA
Holding current	$I_T=1\text{A}$	I_H	≤ 250	mA
Latching current	$I_G=1.2 I_{GT}$	I_L	≤ 300	mA
Triggering gate voltage	$V_D=12\text{V}$ $R_L=30\Omega$	V_{GT}	≤ 1.8	V
Non triggering gate voltage	$V_D=V_{DRM}$ $T_j=125^{\circ}\text{C}$	V_{GD}	≥ 0.25	V
Critical rate of rise of voltage	$V_D=2/3V_{DRM}$ $T_j=125^{\circ}\text{C}$ Gate Open	dv/dt	≥ 1000	$\text{V}/\mu\text{s}$
Thermal resistance	Junction to case Case to heatsink	$R_{th(j-c)}$ $R_{th(c-s)}$	0.19 0.12	$^{\circ}\text{C}/\text{W}$

Mechanical Characteristics

Module size	94mm×34.2mm
Module height	29.5mm
Terminal distance of (1) /(2) /(3)	23mm
Mounting torque(M5)	5±15%Nm
Terminal torque(M6)	5±15%Nm
 T2	  AKMD symbol  AKMH symbol

Performance Curves

FIG.1: Power dissipation vs. on-state current (per thyristor or diode)

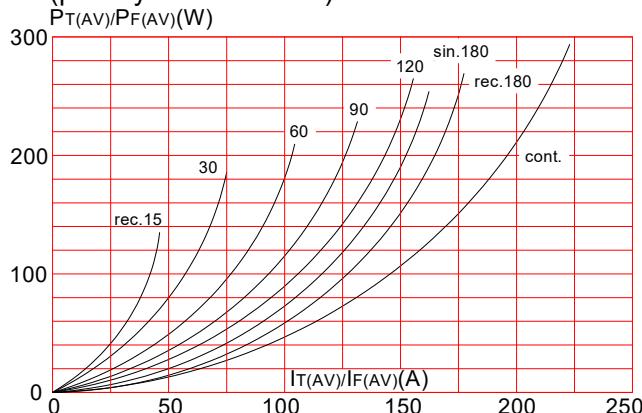


FIG.2: Maximum transient thermal impedance junction to case (per thyristor or diode)

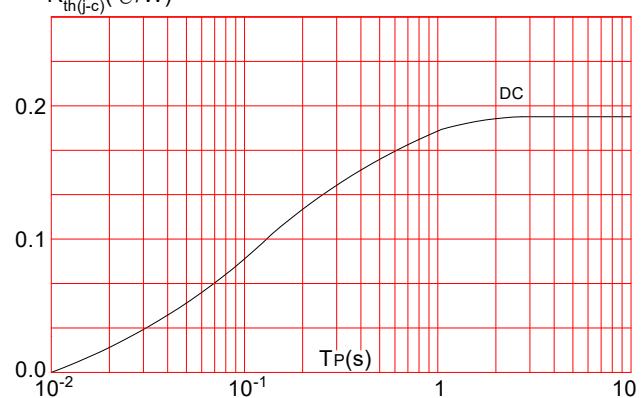


FIG.3: Forward characteristics (per thyristor or diode)

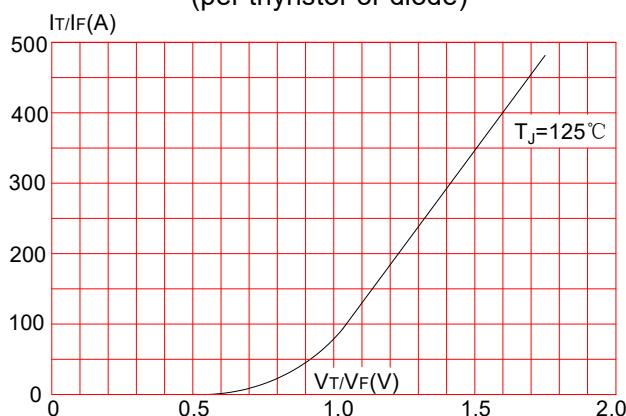
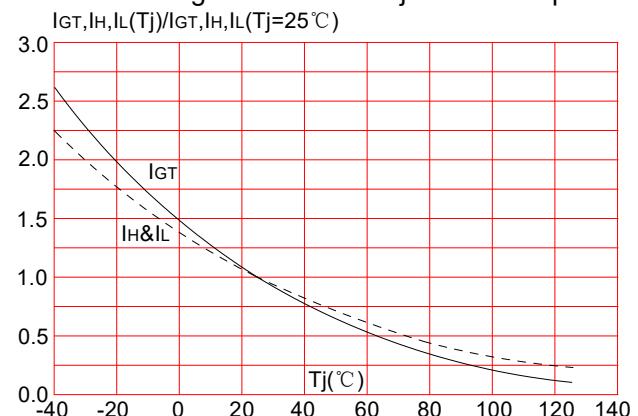


FIG.4: Relative variations of gate trigger current, holding current and latching current versus junction temperature



Ordering Information

AK

MD

162 / 16

Aiko Electronics Technology Co., LTD

MD: Thyristor module

MH: Thyristor and diode module

12: $V_{DSM}/V_{RSM} \geq 1300V$
 16: $V_{DSM}/V_{RSM} \geq 1700V$
 18: $V_{DSM}/V_{RSM} \geq 1900V$

$I_{T(AV)}/I_{F(AV)} = 160A$